



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: Minoru SUZUKI et al.

Serial No.: 10/014,407

Group Art Unit: Not Yet Assigned

Filed: December 14, 2001

Examiner: Not Yet Assigned

For: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING  
A SEMICONDUCTOR DEVICE

PRELIMINARY AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

January 24, 2002

Sir:

This is a Preliminary Amendment for the above-captioned patent application. Please amend the above-captioned patent application as follows:

IN THE SPECIFICATION:

Please replace the paragraph beginning at page 11, line 14, with the following rewritten paragraph:

Referring to FIG. 1(a), first, a semiconductor substrate 9 consisting of high-resistivity N-type silicon single crystal is prepared. Here, a crystal with a resistivity of  $20\Omega\text{cm}$  or more, and less than or equal to  $60\Omega\text{cm}$  (less than or equal to  $2 \times 10^{14}/\text{cm}^3$  and greater than or equal to  $7 \times 10^{13}/\text{cm}^3$  in concentration conversions) was used as the semiconductor substrate 9.

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